

**SEMITOP® 3**

## IGBT Module

**SK30GAD066T**

### Target Data

### Features

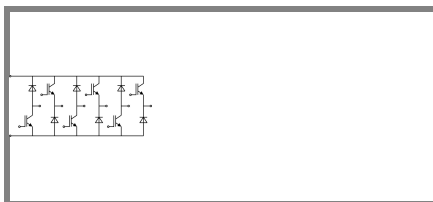
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Trench silicon structure
- High short circuit capability
- Low tail current with low temperature dependence
- Integrated PTC temperature sensor

### Typical Applications\*

- Switching (not for linear use)
- Inverter
- Switched mode power supplies
- UPS

### Remarks

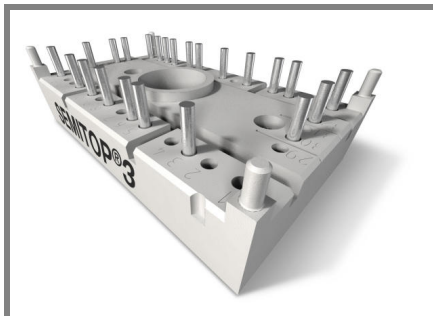
- PTC temp sensor test conditions:  
measuring current: 1 mA  
max measuring current value: 3 mA



**GAD**

Absolute Maximum Ratings		$T_s = 25\text{ °C}$ , unless otherwise specified	
Symbol	Conditions	Values	Units
<b>IGBT</b>			
$V_{CES}$	$T_j = 25\text{ °C}$	600	V
$I_C$	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	38 A
		$T_s = 70\text{ °C}$	31 A
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	60	A
$V_{GES}$		$\pm 20$	V
$t_{psc}$	$V_{CC} = 360\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125\text{ °C}$ $V_{CES} < 600\text{ V}$	6	$\mu\text{s}$
<b>Inverse Diode</b>			
$I_F$	$T_j = 150\text{ °C}$	$T_s = 25\text{ °C}$	A
		$T_s = 80\text{ °C}$	A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$		A
<b>Freewheeling Diode</b>			
$I_F$	$T_j = 175\text{ °C}$	$T_{case} = 25\text{ °C}$	65 A
		$T_{case} = 70\text{ °C}$	51 A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	200	A
<b>Module</b>			
$I_{t(RMS)}$			A
$T_{vj}$		-40 ... +175	$^{\circ}\text{C}$
$T_{stg}$		-40 ... +125	$^{\circ}\text{C}$
$V_{isol}$	AC, 1 min.	2500	V

Characteristics		$T_s = 25\text{ °C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT</b>					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 0,43\text{ mA}$	5	5,8	6,5	V
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$		0,08	mA
		$T_j = 125\text{ °C}$			mA
$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = 30\text{ V}$	$T_j = 25\text{ °C}$		300	nA
		$T_j = 125\text{ °C}$			nA
$V_{CE0}$		$T_j = 25\text{ °C}$	0,9	1	V
		$T_j = 150\text{ °C}$	0,85	0,9	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	18	28	$\text{m}\Omega$
		$T_j = 150\text{ °C}$	27	38	$\text{m}\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 30\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	1,45	1,85	V
		$T_j = 150\text{ °C}_{chiplev.}$	1,65	2,05	V
$C_{ies}$	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$			nF
$C_{oes}$					nF
$C_{res}$					nF
$t_{d(on)}$	$R_{Gon} = 22\ \Omega$	$V_{CC} = 300\text{ V}$ $I_C = 30\text{ A}$	1,24		ns
$t_r$					ns
$E_{on}$					mJ
$t_{d(off)}$	$R_{Goff} = 22\ \Omega$	$T_j = 150\text{ °C}$ $V_{GE} = \pm 15\text{ V}$	1,48		ns
$t_f$					ns
$E_{off}$					mJ
$R_{th(j-s)}$	per IGBT		1,8		K/W



**SEMITOP<sup>®</sup> 3**

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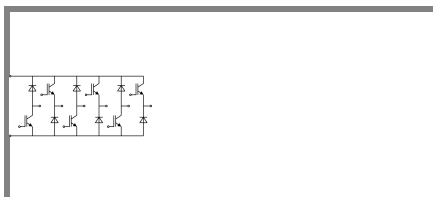
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measuring current: 1 mA  
max measuring current value: 3 mA

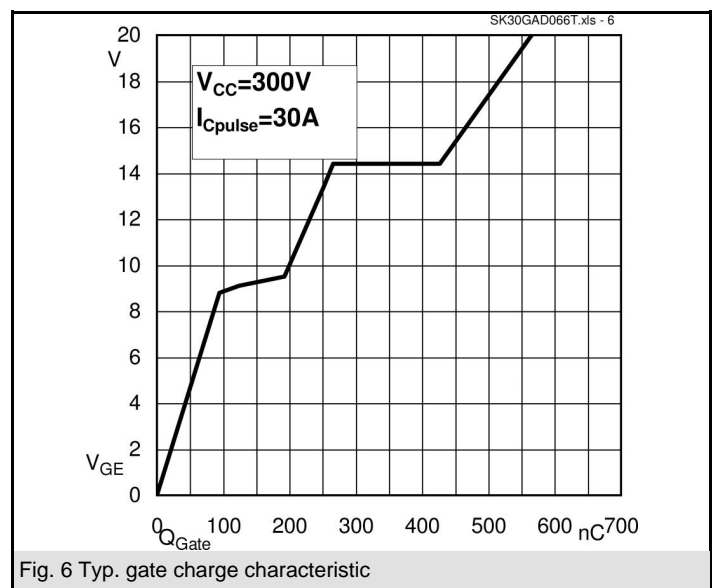
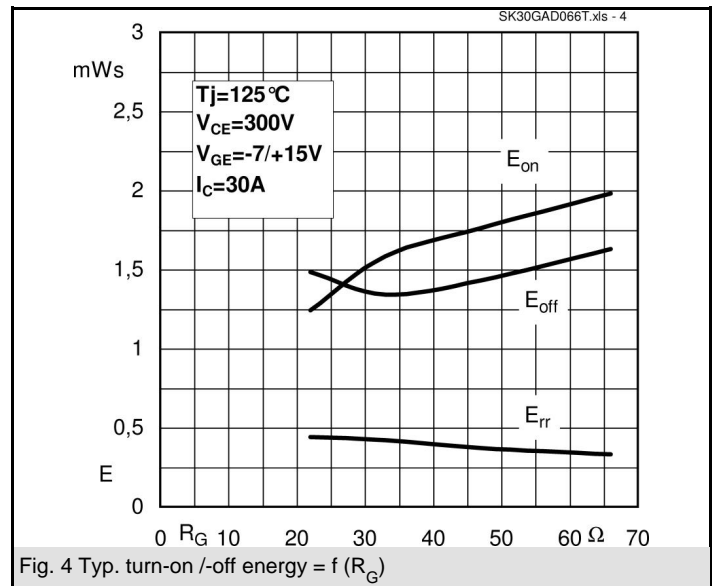
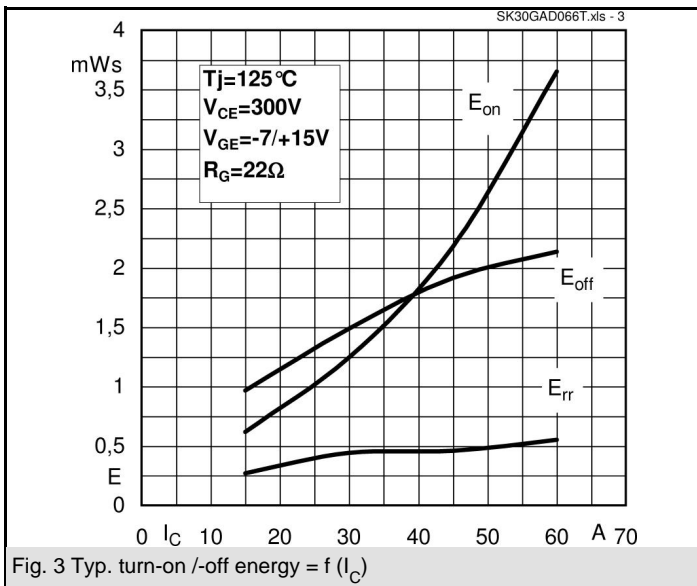
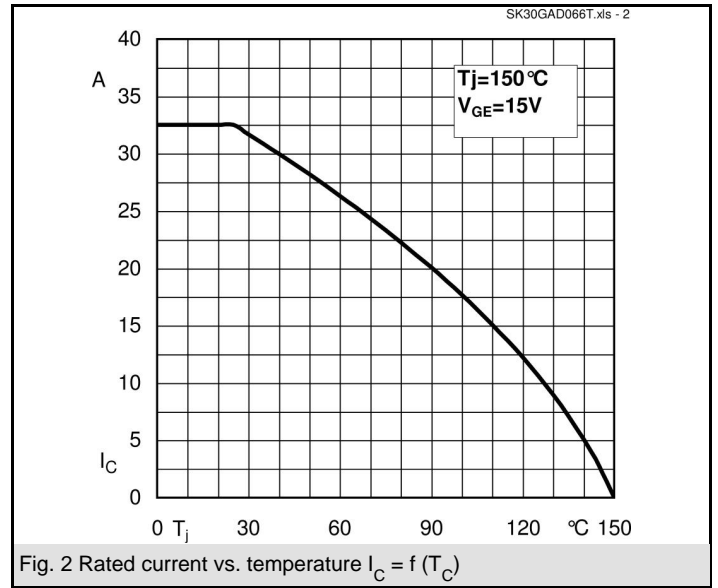
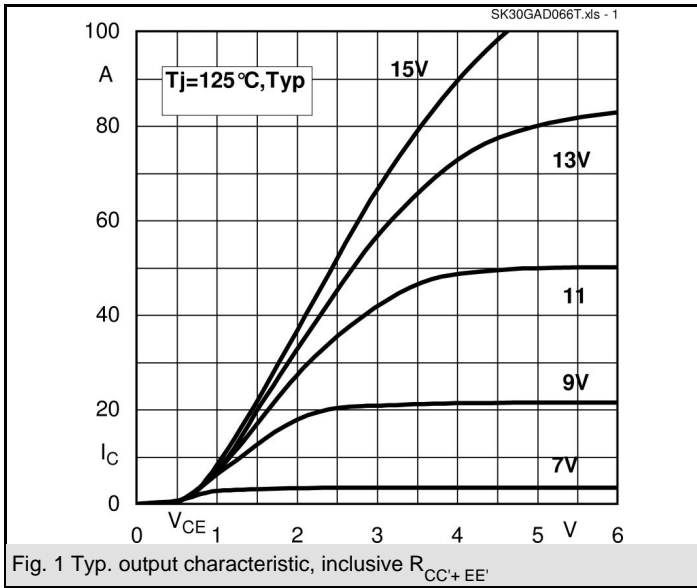


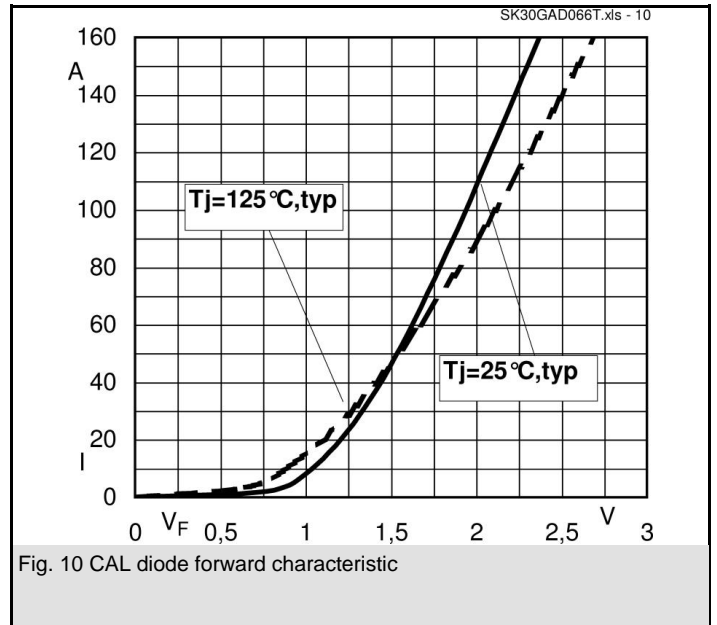
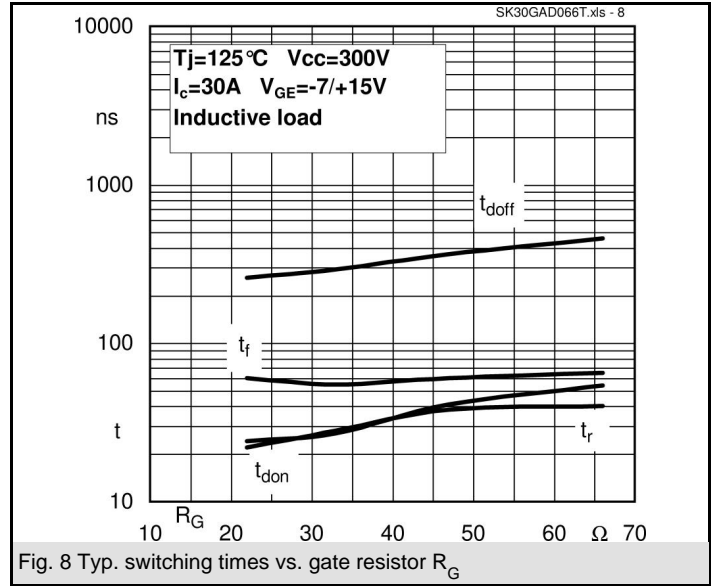
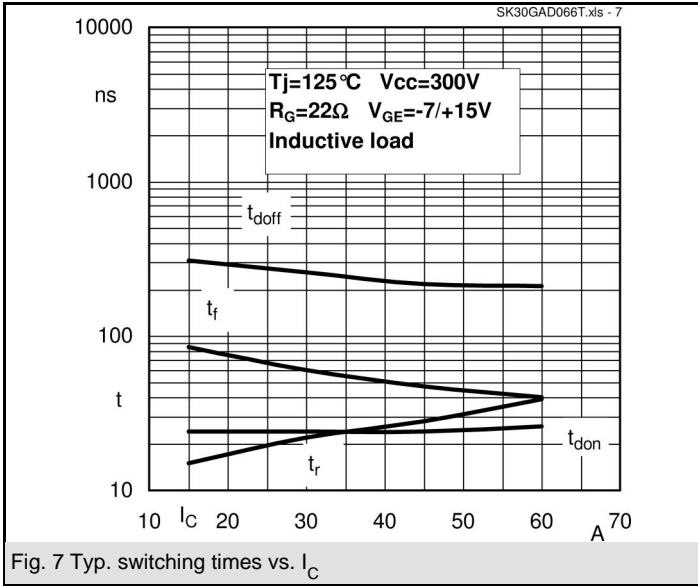
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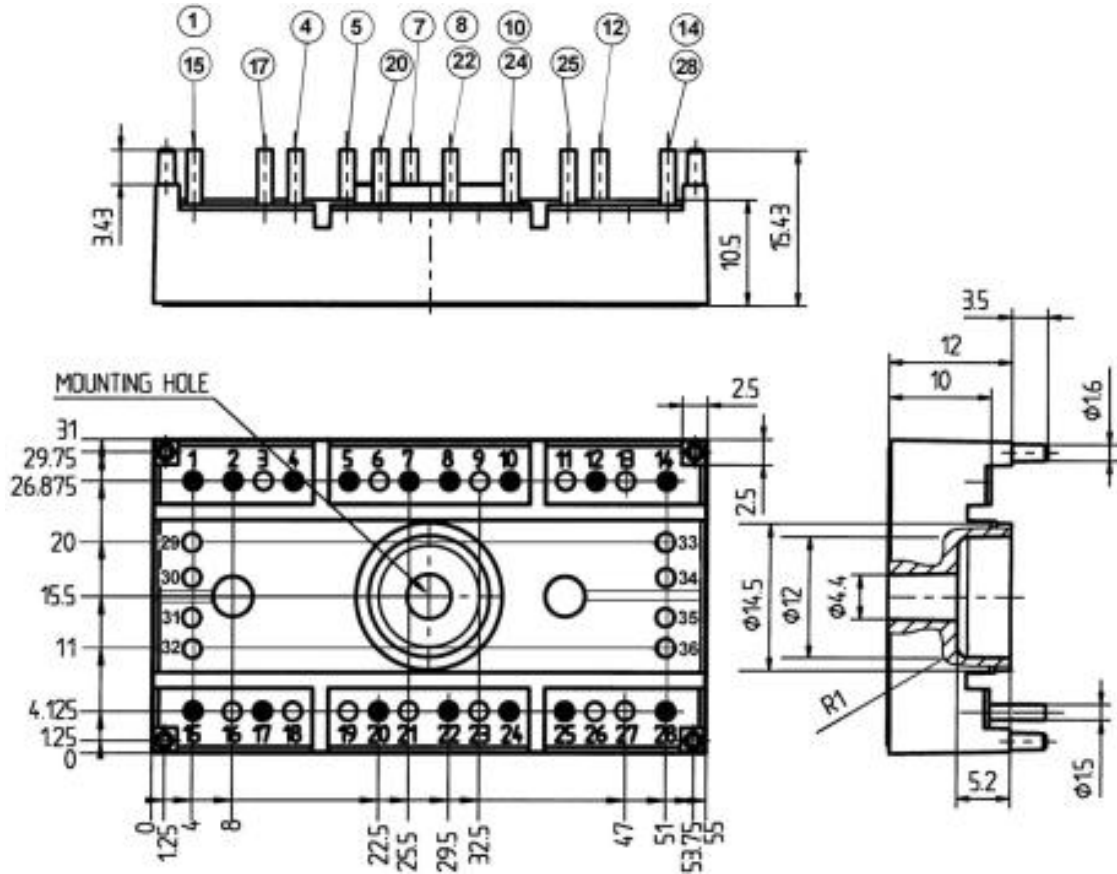
Characteristics						
Symbol	Conditions	min.	typ.	max.	Units	
<b>Freewheeling Diode</b>						
$V_F = V_{EC}$	$I_{Fnom} = 30 \text{ A}; V_{GE} = 0 \text{ V}$		$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	1,3	1,5	V
			$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$	1,2	1,45	V
$V_{F0}$			$T_j = 125 \text{ }^\circ\text{C}$	0,85	0,9	V
$r_F$			$T_j = 125 \text{ }^\circ\text{C}$	9	16	m $\Omega$
$I_{RRM}$	$I_F = 30 \text{ A}$		$T_j = 125 \text{ }^\circ\text{C}$	3		A
$Q_{rr}$	$di/dt = -500 \text{ A}/\mu\text{s}$			3		$\mu\text{C}$
$E_{rr}$	$V_{CC} = 300\text{V}$			0,44		mJ
$R_{th(j-s)FD}$	per diode				1,2	K/W
$M_s$	to heat sink M1	2,25		2,5		Nm
w			30			g
<b>Temperature sensor</b>						
$R_{ts}$	3%, $T_r = 25 (100)^\circ\text{C}$		1000 (1670)			$\Omega$

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

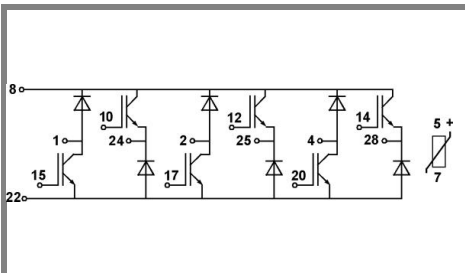
\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.







Case T57 (Suggested hole diameter, in the PCB, for solder pins and plastic mounting pins: 2mm)



Case T 57

GAD